

# Computational Microelectronics

## Lecture 14 Poisson Equation

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# Nonlinear Poisson Equation

# Nonlinear Poisson equation

- In the last lectures,
  - Laplace equation
  - Source-free Poisson equation
  - Poisson equation with fixed charges
  - We are now ready to solve the nonlinear Poisson equation:

$$\nabla \cdot [\epsilon(\mathbf{r}) \nabla \phi] + qn_{int}(\mathbf{r}) \exp\left(-\frac{\phi(\mathbf{r})}{V_T}\right) - qn_{int}(\mathbf{r}) \exp\left(\frac{\phi(\mathbf{r})}{V_T}\right) + qN_{dop}^+(\mathbf{r}) = 0$$

# Discretization

- When the nonlinear Poisson equation is considered,
  - We have additional terms:

$$\epsilon(x_{i+0.5}) \frac{\phi(x_{i+1}) - \phi(x_i)}{x_{i+1} - x_i} - \epsilon(x_{i-0.5}) \frac{\phi(x_i) - \phi(x_{i-1})}{x_i - x_{i-1}} + q \left( n_{int} \exp\left(-\frac{\phi(x_i)}{V_T}\right) - n_{int} \exp\left(\frac{\phi(x_i)}{V_T}\right) + N_{dop}^+(x_i) \right) (x_{i+0.5}$$

# Double-gate example

- Electrostatic potential

- Even when  $V_G = 0$  V, the boundary values of  $\phi$  are not 0 V. (0.33374 V in this example)

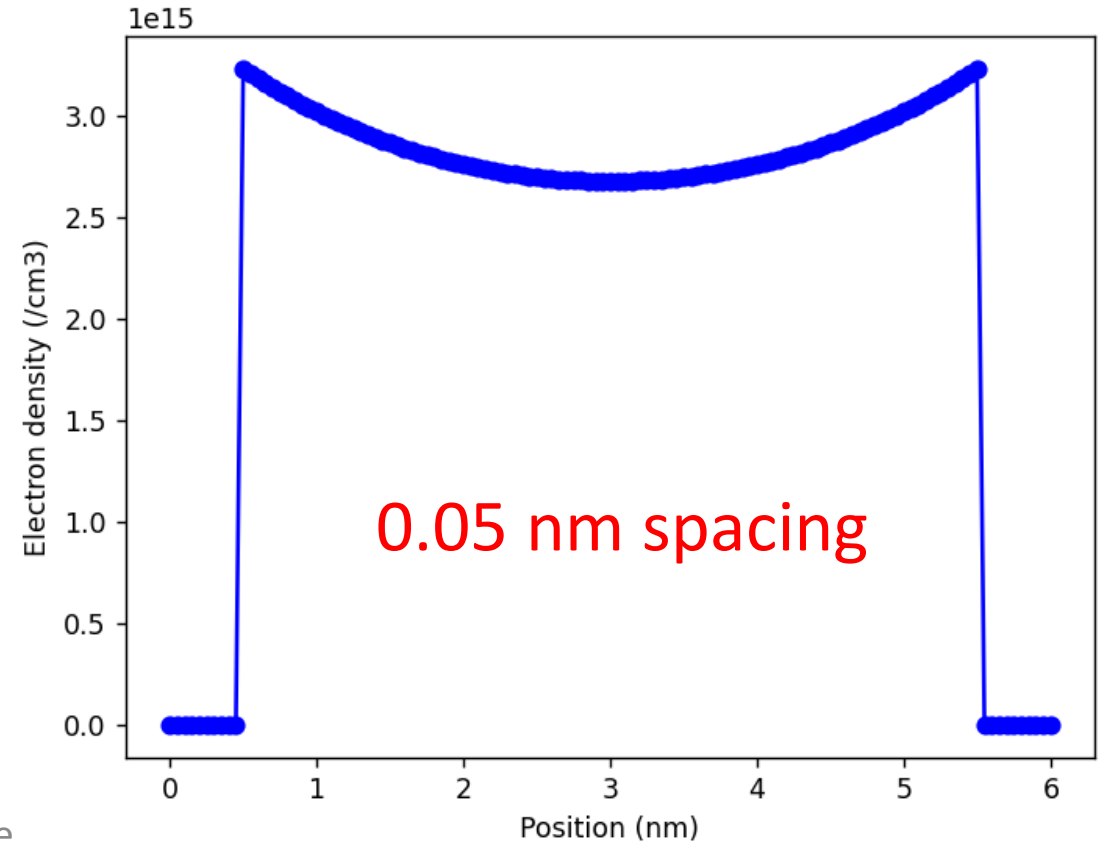
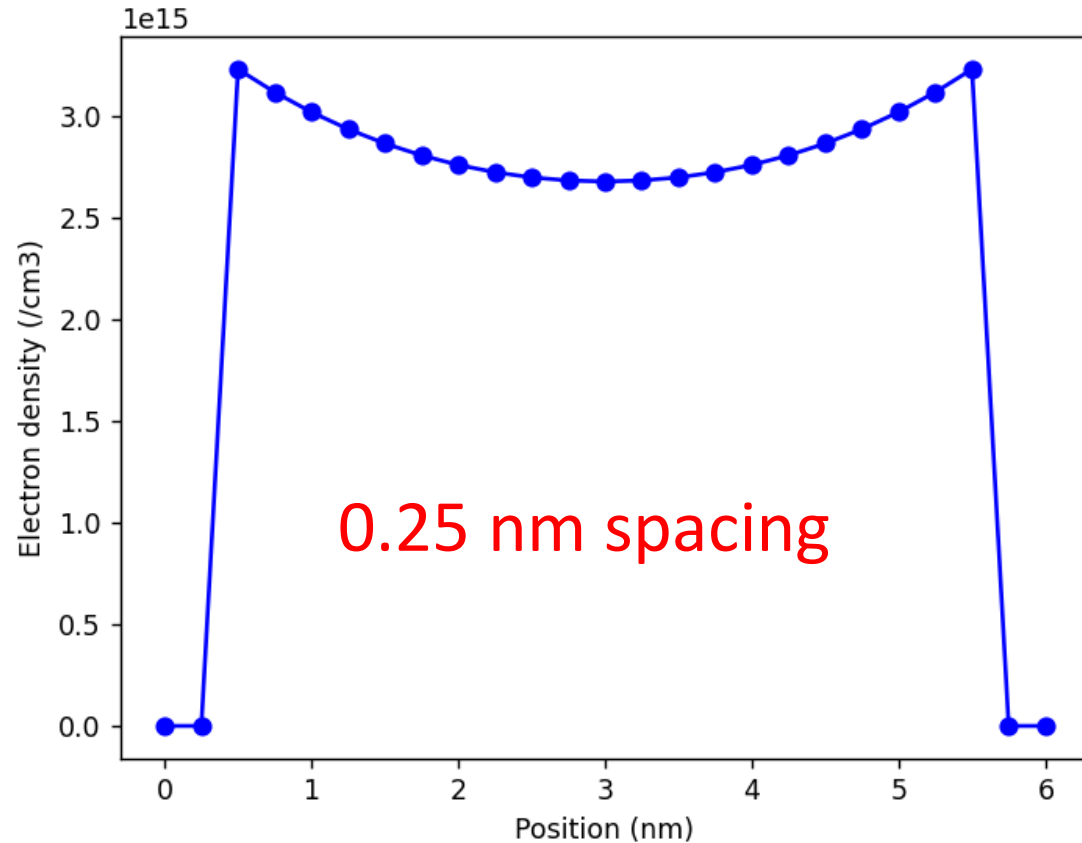
$$-q\phi + (E_{Vac} - E_i) = \Phi$$

Workfunction

$\sim 4.63$  eV in silicon

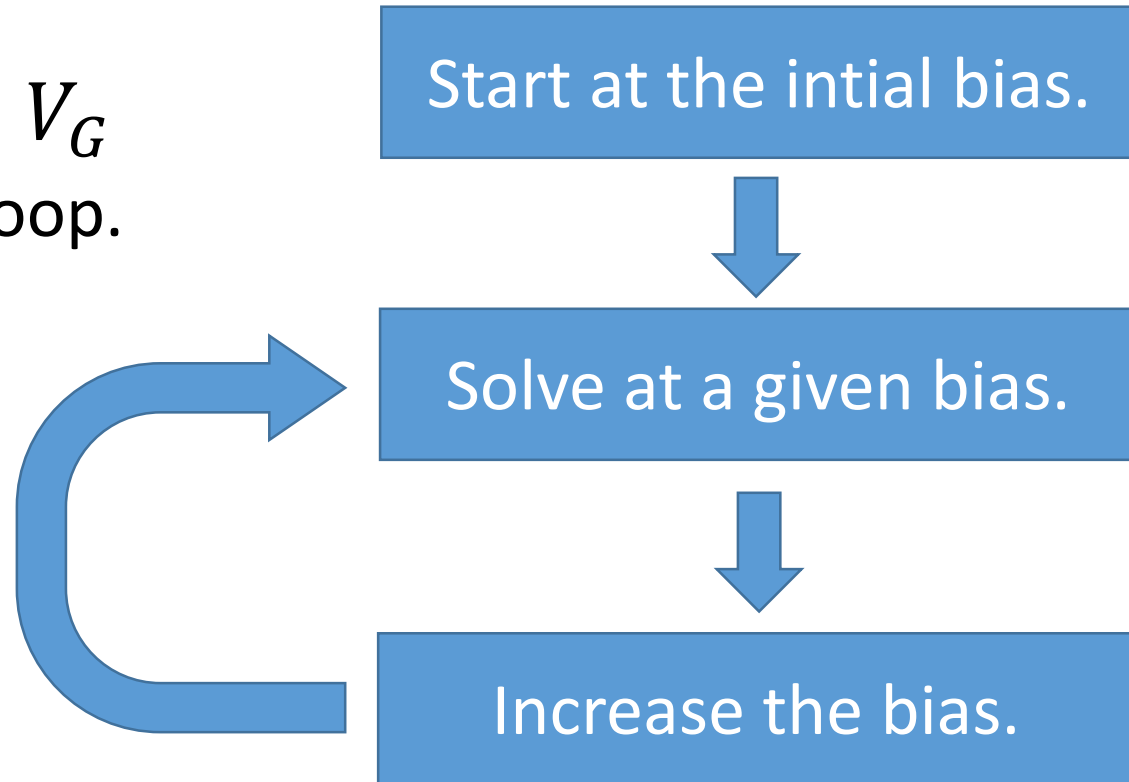
# Its solution

- Electron density at  $V_G = 0$  V
  - Change the number of grid points.



# Bias ramping

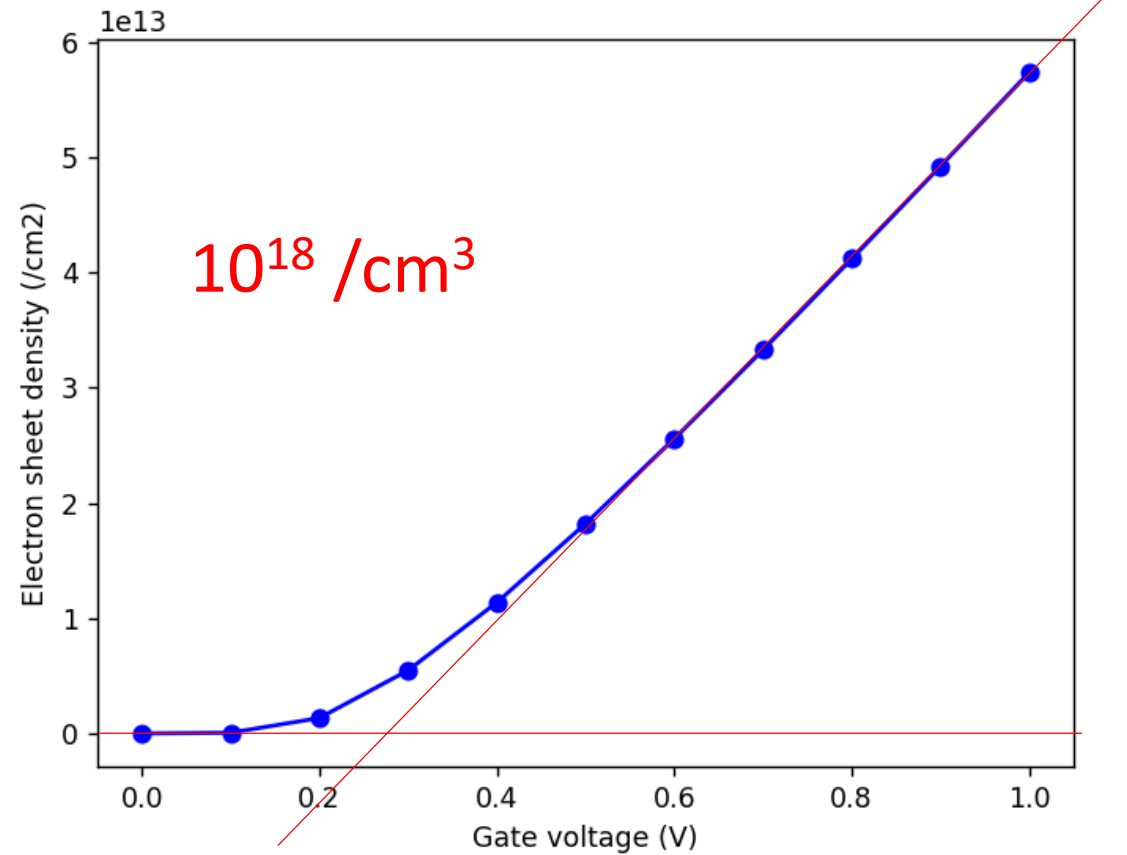
- Ramp up the gate voltage,  $V_G$ 
  - Simply add an outermost loop.



- The boundary values of  $\phi$  are given as
$$\phi = \phi_0 + V_G$$

# Its solution

- Inversion charge as a function of  $V_G$ 
  - It can be written as  $qN_{inv} = C_{ox}(V_G - V_{TH})$





# Thank you!